

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI TVU150 is Designed for

FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	25 A
V_{CEO}	28 V
V_{CES}	60 V
V_{EBO}	3.5 V
P_{DISS}	300 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.55 °C/W

PACKAGE STYLE .400 BAL FLG(C)

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.210 / 5.33	
C	.120 / 3.05	.130 / 3.30
D	.380 / 9.65	.390 / 9.91
E	.780 / 19.81	.820 / 20.83
F	.435 / 11.05	
G	1.090 / 27.69	
H	1.335 / 33.91	1.345 / 34.16
I	.003 / 0.08	.007 / 0.18
J	.060 / 1.52	.070 / 1.78
K	.082 / 2.08	.100 / 2.54
L		.205 / 5.21
M	.395 / 10.03	.407 / 10.34
N	.850 / 21.59	.870 / 22.10

ORDER CODE: ASI10652

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA	26	30		V
BV_{CER}	I _C = 100 mA R _{BE} = 200 Ω	35	40		V
BV_{CES}	I _C = 50 mA	60	80		V
BV_{EBO}	I _E = 10 mA	3.5	4.0		V
I_{CES}	V _{CE} = 30 V			10	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	30	45	120	---
C_{OB}	V _{CB} = 26 V f = 1.0 MHz		75		pF
P_G IMD₁	V _{CC} = 26 V I _{CQ} = 2 X 3000 mA f = 860 MHz P _{OUT} = 40 W	11 -52	9.0		dB dBc
Load Mismatch	V _{CC} = 26 V I _{CQ} = 2 X 150 mA P _{OUT} = 150 W PEP VSWR = 5:1 @ all phase angles	No Degradation in Output Power			